

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

GreenMOS[®]



Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

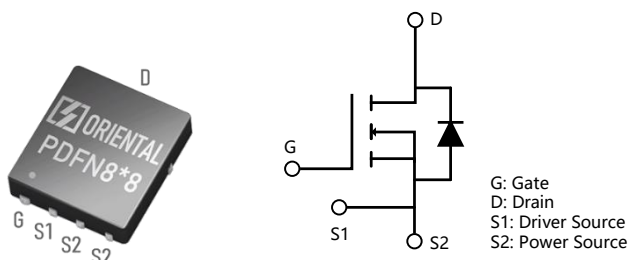
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, \min} @ T_{j(max)}$	650	V
I_D, pulse	82	A
$R_{DS(ON), \max} @ V_{GS}=10V$	65	$m\Omega$
Q_g	54	nC

Marking Information

Product Name	Package	Marking
OSG60R065JT3F	PDFN 8×8	OSG60R065JT3

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	48	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		30.4	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, \text{pulse}}$	82	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	48	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, \text{pulse}}$	82	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	181	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	176	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\ldots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.69	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
		650				$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	3.5		4.5	V	$V_{DS}=V_{GS}$, $I_D=1\text{ mA}$
Drain-source on-state resistance	$R_{DS(on)}$		60	65	m Ω	$V_{GS}=10\text{ V}$, $I_D=16\text{ A}$
			151			$V_{GS}=10\text{ V}$, $I_D=16\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$
Gate resistance	R_G		9.5		Ω	$f = 1\text{ MHz}$, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		3181		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		187		pF	
Reverse transfer capacitance	C_{rss}		4.3		pF	
Effective output capacitance, energy related	$C_{o(er)}$		118		pF	$V_{GS}=0\text{ V}$, $V_{DS}=0\text{ V}-400\text{ V}$
Effective output capacitance, time related	$C_{o(tr)}$		656		pF	
Turn-on delay time	$t_{d(on)}$		24		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=20\text{ A}$
Rise time	t_r		27		ns	
Turn-off delay time	$t_{d(off)}$		74		ns	
Fall time	t_f		4.4		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		54		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=20\text{ A}$
Gate-source charge	Q_{gs}		15.7		nC	
Gate-drain charge	Q_{gd}		15.3		nC	
Gate plateau voltage	$V_{plateau}$		5.8		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=48\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		349		ns	$V_R=400\text{ V}$, $I_S=20\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		6.5		μC	
Peak reverse recovery current	I_{rrm}		37.5		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^{\circ}\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=80\text{ mH}$, starting $T_j=25\text{ }^{\circ}\text{C}$.

Electrical Characteristics Diagrams

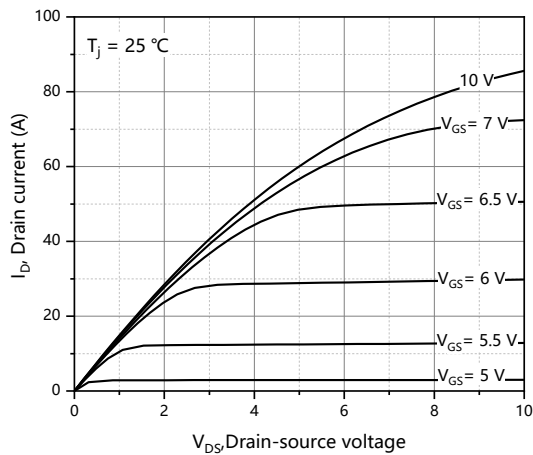


Figure 1. Typ. output characteristics

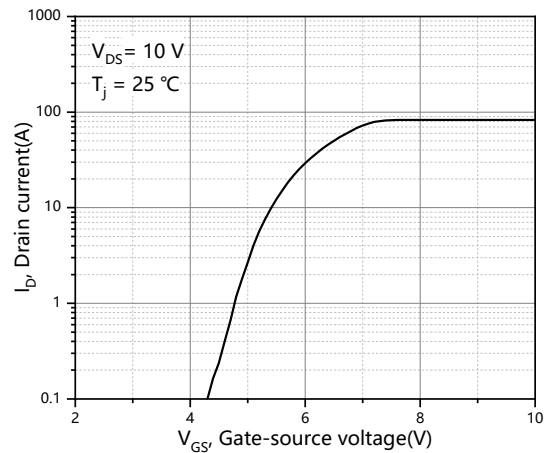


Figure 2. Typ. transfer characteristics

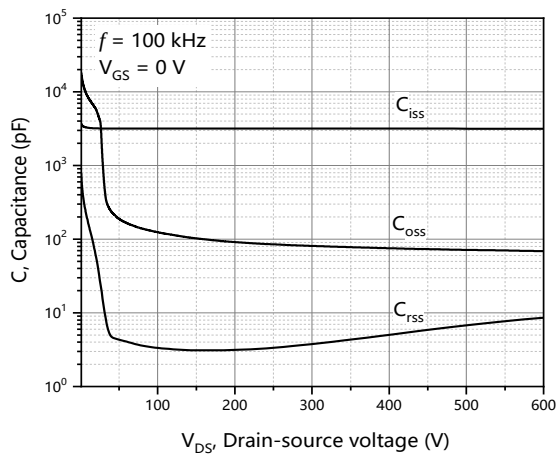


Figure 3. Typ. capacitances

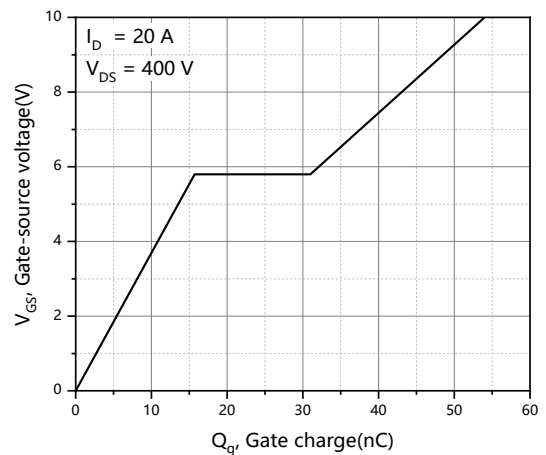


Figure 4. Typ. gate charge

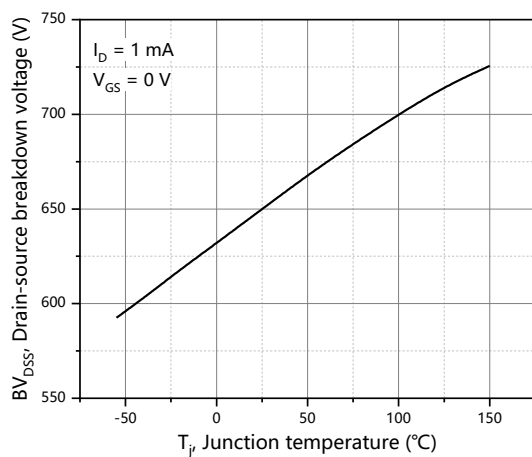


Figure 5. Drain-source breakdown voltage

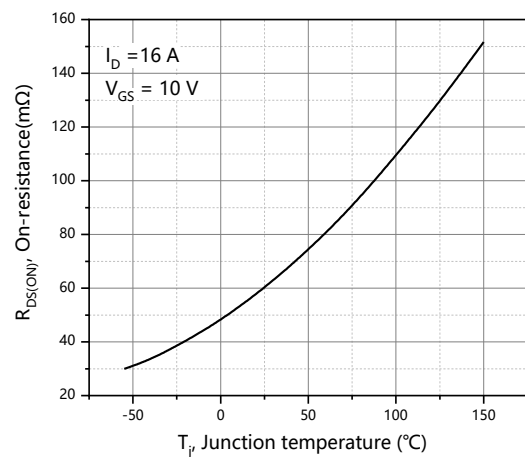


Figure 6. Drain-source on-state resistance

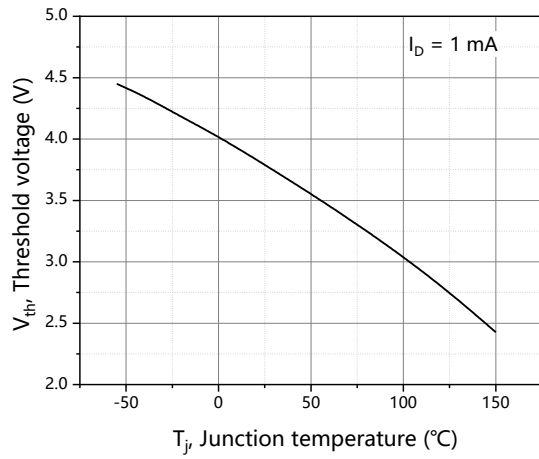


Figure 7. Threshold voltage

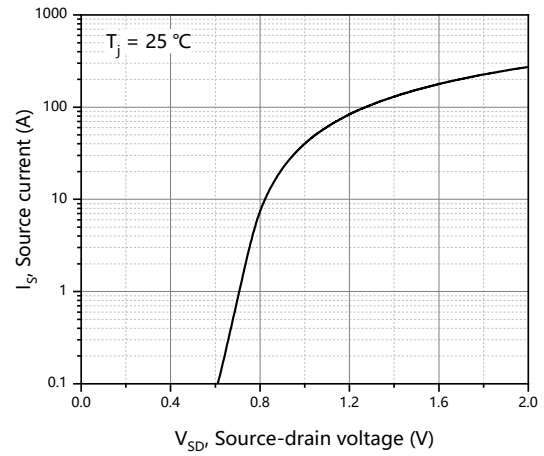


Figure 8. Forward characteristic of body diode

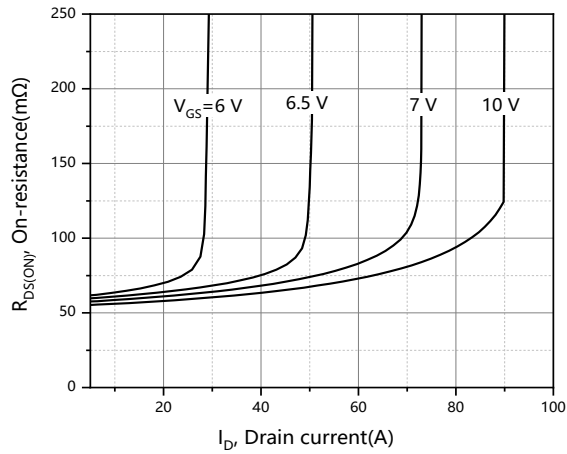


Figure 9. Drain-source on-state resistance

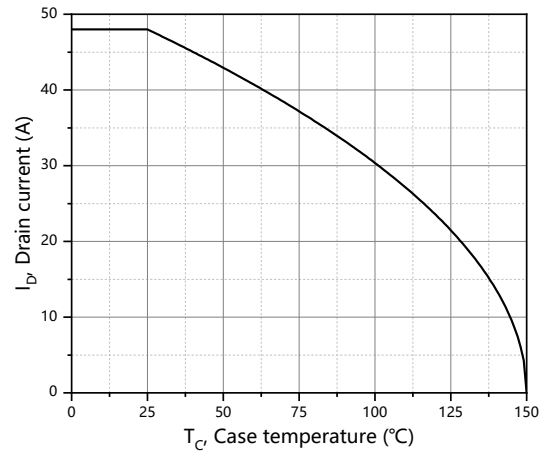


Figure 10. Drain current

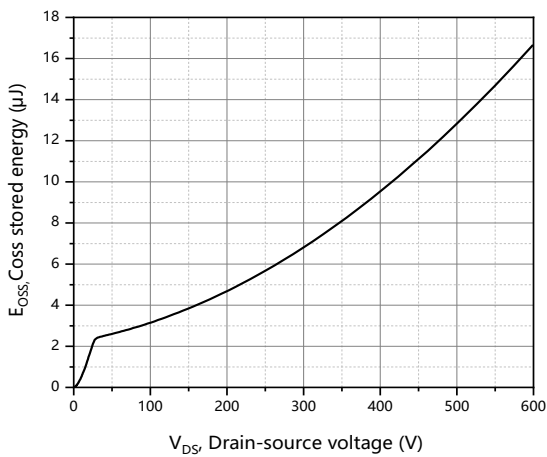


Figure 11. Typ. Coss stored energy

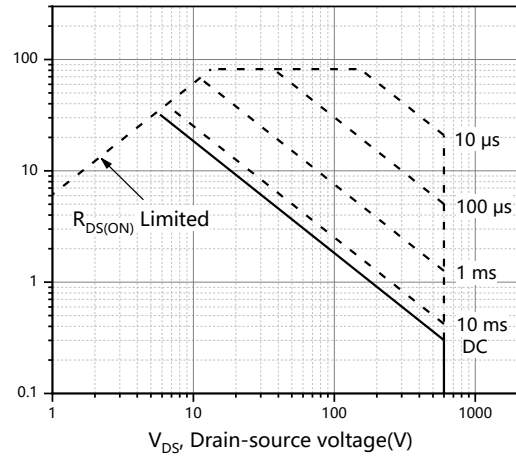


Figure 12. Safe operation area for $T_C=25$ °C

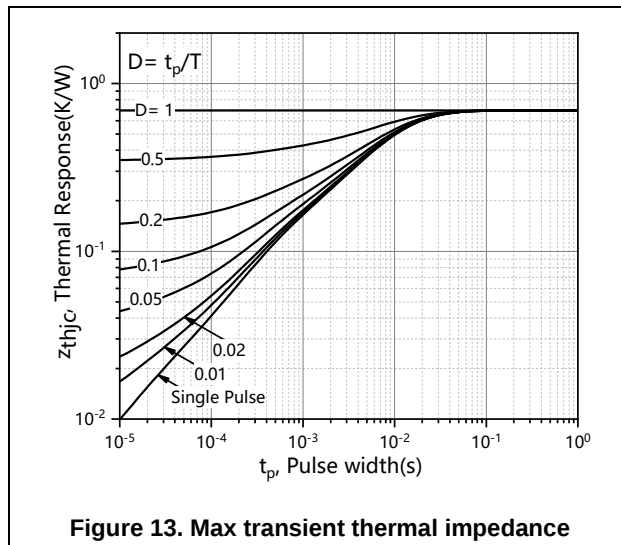


Figure 13. Max transient thermal impedance

Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

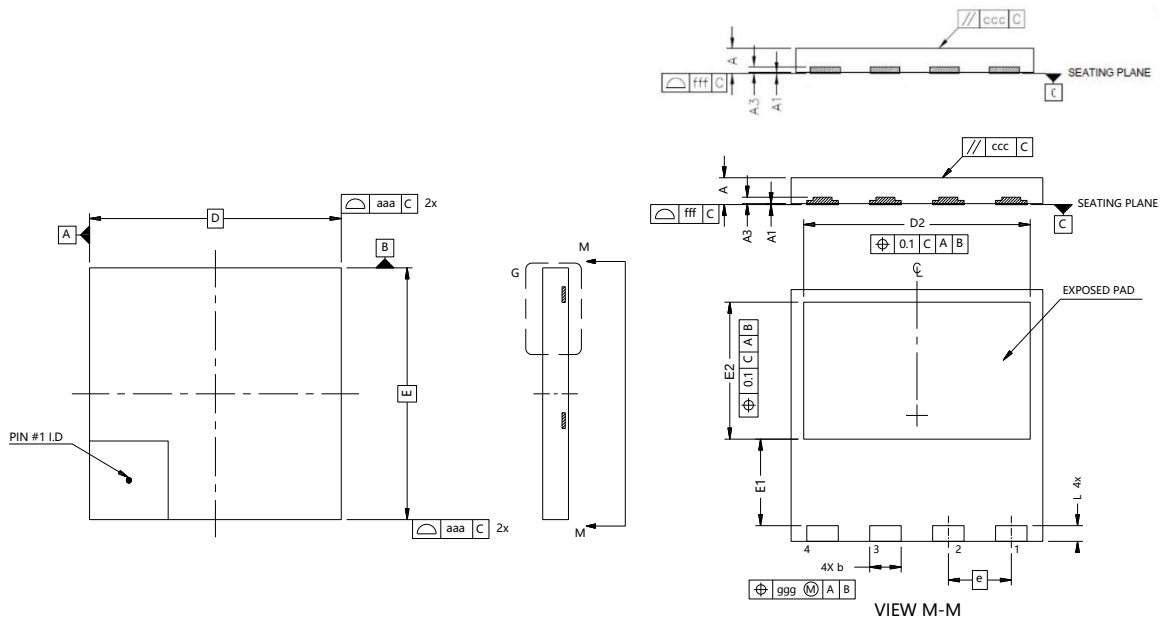


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm	
	Min	Max
A	0.75	0.95
A1	0.00	0.05
A3	0.10	0.30
b	0.90	1.10
D	7.90	8.10
E	7.90	8.10
D2	7.10	7.30
E1	2.65	2.85
E2	4.25	4.45
e	2.0 BSC	
L	0.40	0.60
aaa	0.1	
ggg	0.05	
ccc	0.05	
fff	0.05	

Version 1: PDFN 8×8-S package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
PDFN 8×8-S	3000	1	3000	10	30000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG60R065JT3F	PDFN 8×8	yes	yes	yes

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